大学英语3-题库

1、使大众化

A, democrat

B, democracy

C, democratize

D, democratic

答案: C

2、纳米片技术

A, nanosheet technology

B, nanometer technology

答案: A

3、底部介电隔离

A, bottom electric isolation

B, bottom dielectric isolation

答案: B

4、高性能计算

A, high-performance computing

B, high efficency caculation

答案: A

5、阈值电压

A, threshold voltages

B, source voltages

答案: A

6、混合云

A, Multi-cloud

B, Hybrid Cloud

答案: B

7、便携式设备

A, portable devices

B, convenient devices

答案: A

8、【单选题】anticipate

- 预计 A,
- B、反对
- C、呼吁
- D、筹划
- 答案: A

9、【单选题】transistor

- A、运输者
- B、晶体管
- C、译员
- D、导体
- 答案: B

10、【单选题】implement

- A、 补充
- B、阻碍
- C、实施
- D、投资
- 答案: C

11、【单选题】immunity

- 免除 A,
- B、共享
- C、 牵连 D、 用具
- 答案: A

12、【单选题】resistor

- A、共振器
- B、电阻器
- C、恢复者
- D、呼吸器
- 答案: B

13、【单选题】device

- 设计 A,
- B、转交
- C, 发明
- 设备

答案: D

14、【单选题】promising

- A、承诺的
- B、特有的
- C、 大有希望的 D、 合乎体统的

答案: C

15、【单选题】autonomous

- A、 备用的
- B、有自主能力的
- C、自动提示的
- D、独断专行的

答案: B

16、【单选题】breakthrough

- 突破 A,
- B、爆发
- C、结束
- D、破裂

答案: A

17、【单选题】horizontal

- A、水平的
- B、倾斜的
- C、 垂直的 D、 弧形的

答案: A

18、【单选题】优化

- A, optimistic
- B, optimize
- C, optimal
- D, optimum

答案: B

19、【单选题】限制

- A, constraint
- B, constant
- C, constructor
- D, contempt

20、【单选题】阈值电压	
A、 threshold voltages B、 source voltages C、 threshold pressure D、 source pressure 答案: A	
21、【单选题】While these all represent breakthrough developments in enabling 2-nm node chip it does of interconnect crowding. A、rise the question B、answer the question C、reject the question D、raise the question 答案: D	
22、【单选题】Potential benefits of these advanced 2-nm chips will befor today's most advanced semiconductors. A、extraodinary B、exponential C、exceptional D、exclusive 答案: B	
23、【单选题】While IBM's manufacturing partner, Samsung, does plan to use nanosheet technology for it 3-nm chips, IBM them both by using nanosheets and going down another step to 2-nm node. A、stood out B、exceled C、beyond D、outdid 答案: D	
24、【单选题】What does the underlined phrase mean? Khare <u>was reticent to discuss</u> the specifics of standard cell library density and SRAM and only offer that it will likely follow the same bench mark with 7-,5nm nodes. A、refuse to talk about B、like to disclose C、keep talking about D、attempt to indicate 答案: A	l
25、【单选题】The foundation of the chip is nanosheet technology in which each transistor is made up of, each only a few nanometer stick and completel surrounded by a gate. A、three stacked vertical sheets of silicon B、three layered horizontal sheets of silicon C、three layered vertical sheets of silicon D、three stacked horizontal sheets of silicon S条: D	. y